

General Description

- Bottom Source Technology
- Very Low $R_{DS(ON)}$
- High Current Capability
- RoHS and Halogen-Free Compliant

Applications

- DC/DC Converters in PC, Servers
- Point of load Converters

Product Summary

	Q1	Q2
V_{DS}	25V	25V
I_D (at $V_{GS}=10V$)	17A	34A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 4.6m Ω	< 1.4m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 6m Ω	< 1.7m Ω

100% UIS Tested
 100% Rg Tested

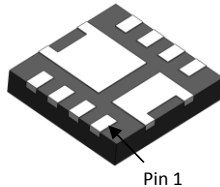


DFN3.3x3.3A

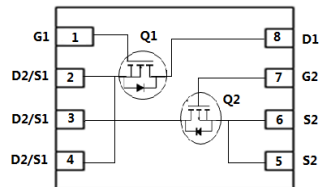
Top View



Bottom View



Top View



Transparent View



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AONE36132	DFN3.3x3.3A	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Max Q1	Max Q2	Units
Drain-Source Voltage	V_{DS}	25	25	V
Gate-Source Voltage	V_{GS}	± 12	± 12	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	60 ^G	A
		$T_C=100^\circ\text{C}$	38	
Pulsed Drain Current ^C	I_{DM}	160	200	
Continuous Drain Current	I_{DSM}	$T_A=25^\circ\text{C}$	17	A
		$T_A=70^\circ\text{C}$	13.5	
Avalanche Current ^C	I_{AS}	48	60	A
Avalanche energy $L=0.01\text{mH}$ ^C	E_{AS}	12	18	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	25	W
		$T_C=100^\circ\text{C}$	10	
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ\text{C}$	2	W
		$T_A=70^\circ\text{C}$	1.3	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ Q1	Typ Q2	Max Q1	Max Q2	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	50	40	60	50	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A D}		75	65	90	80	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	4	2.5	5	3.5	$^\circ\text{C/W}$

Q1 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	25			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =25V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±12V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	1.4	1.8	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =17A T _J =125°C		3.8	4.6	mΩ
		V _{GS} =4.5V, I _D =15A		5.3	6.4	
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =17A		100		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				30	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =12.5V, f=1MHz		880		pF
C _{oss}	Output Capacitance			250		pF
C _{rss}	Reverse Transfer Capacitance			55		pF
R _g	Gate resistance	f=1MHz	0.35	0.7	1.05	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =12.5V, I _D =17A		14.5	21	nC
Q _g (4.5V)	Total Gate Charge			6.5	10	nC
Q _{gs}	Gate Source Charge			2.5		nC
Q _{gd}	Gate Drain Charge			2.5		nC
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =12.5V, R _L =0.75Ω, R _{GEN} =3Ω		4.5		ns
t _r	Turn-On Rise Time			3.5		ns
t _{D(off)}	Turn-Off Delay Time			20		ns
t _f	Turn-Off Fall Time			2.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =17A, di/dt=500A/μs		9		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =17A, di/dt=500A/μs		11.5		nC

- A. The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on R_{θJA} ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.
- G. The maximum current rating is package limited.
- H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

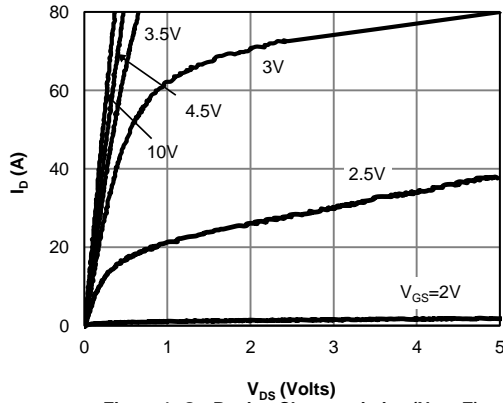


Figure 1: On-Region Characteristics (Note E)

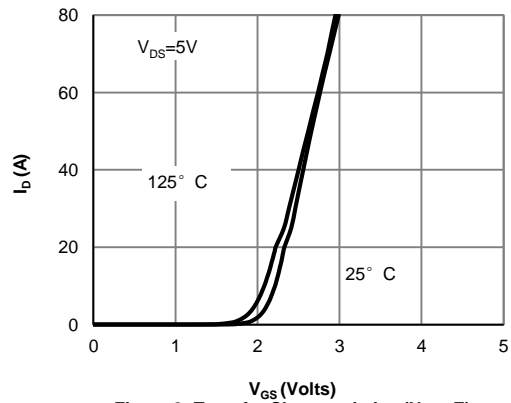


Figure 2: Transfer Characteristics (Note E)

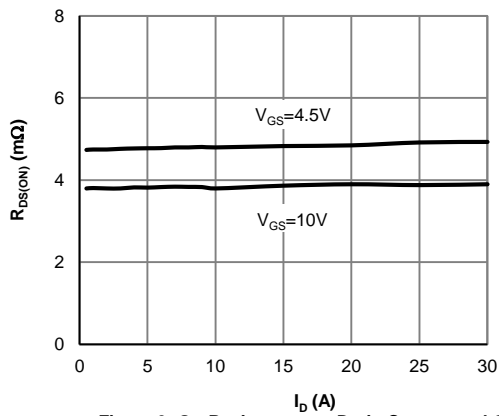


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

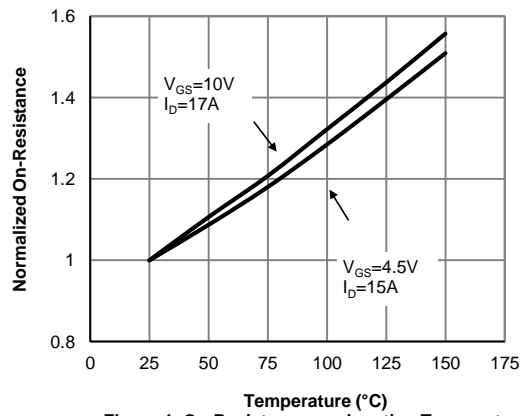


Figure 4: On-Resistance vs. Junction Temperature (Note E)

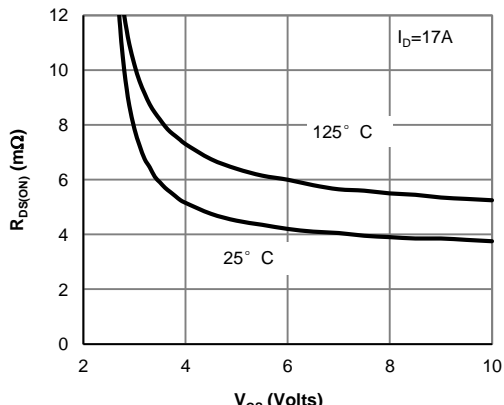


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

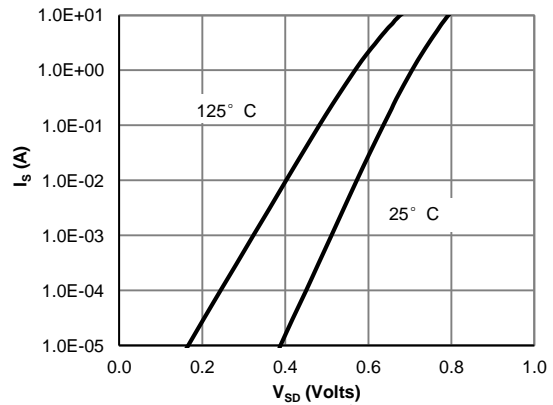


Figure 6: Body-Diode Characteristics (Note E)

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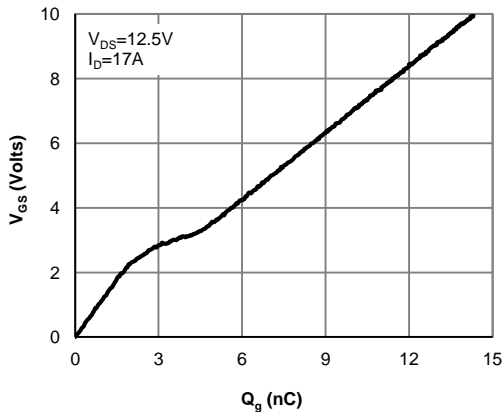


Figure 7: Gate-Charge Characteristics

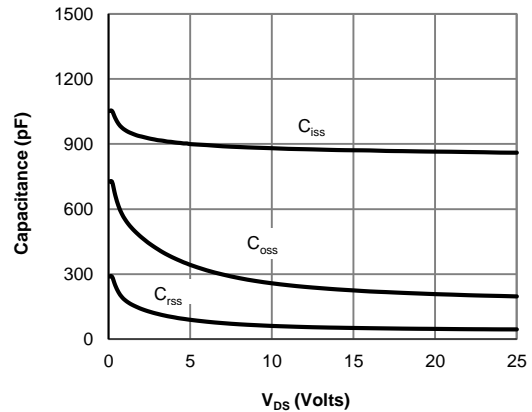


Figure 8: Capacitance Characteristics

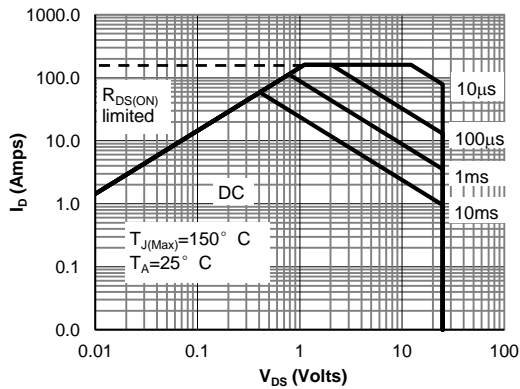


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

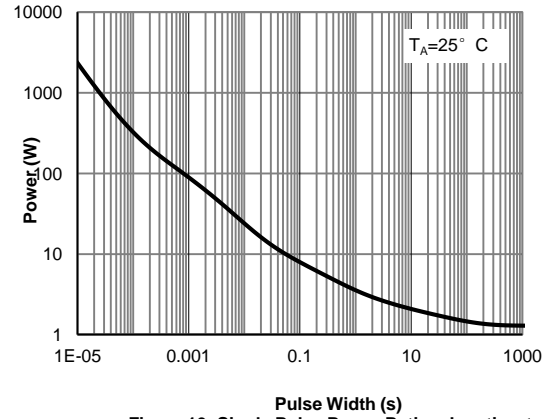


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note H)

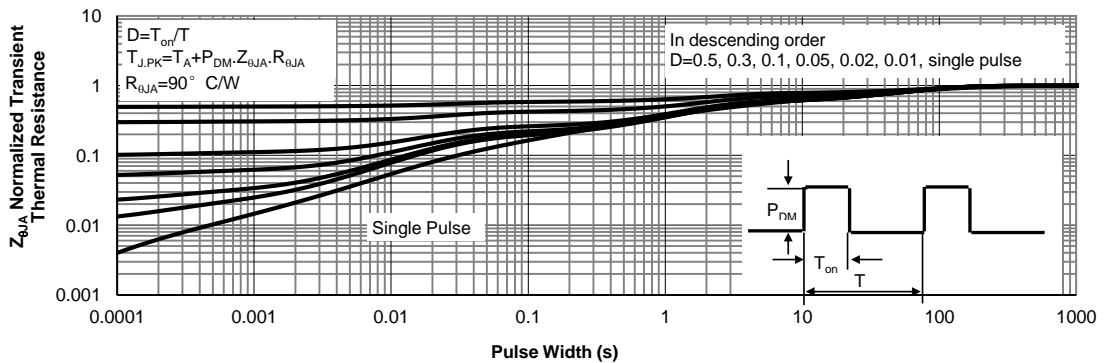


Figure 11: Normalized Maximum Transient Thermal Impedance (Note H)

Q2 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	25			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =25V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±12V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1	1.4	1.8	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		1.1	1.4	mΩ
		V _{GS} =4.5V, I _D =20A		1.3	1.7	
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		165		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				40	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =12.5V, f=1MHz		3215		pF
C _{oss}	Output Capacitance			860		pF
C _{riss}	Reverse Transfer Capacitance			200		pF
R _g	Gate resistance	f=1MHz	0.4	0.8	1.2	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =12.5V, I _D =20A		55	80	nC
Q _{g(4.5V)}	Total Gate Charge			25	35	
Q _{gs}	Gate Source Charge			9.5		
Q _{gd}	Gate Drain Charge			5		
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =12.5V, R _L =0.6Ω, R _{GEN} =3Ω		8		ns
t _r	Turn-On Rise Time			5.5		
t _{D(off)}	Turn-Off DelayTime			39.5		
t _f	Turn-Off Fall Time			7		
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=500A/μs		16		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=500A/μs		33.5		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} t_s ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T_{J(MAX)}=150° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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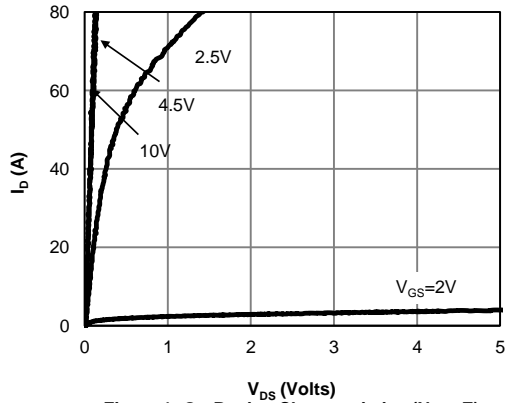


Figure 1: On-Region Characteristics (Note E)

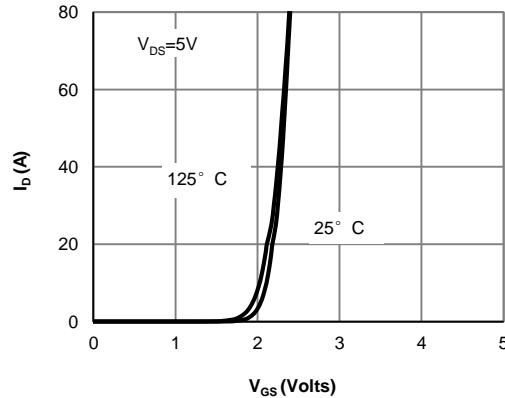


Figure 2: Transfer Characteristics (Note E)

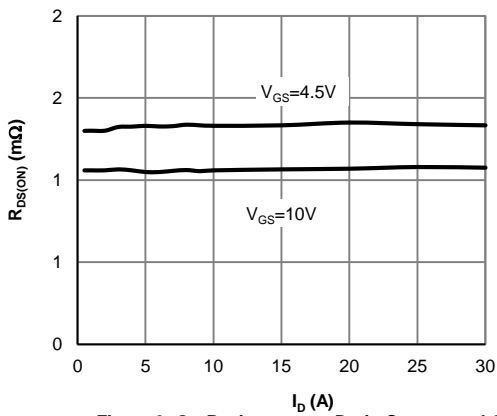


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

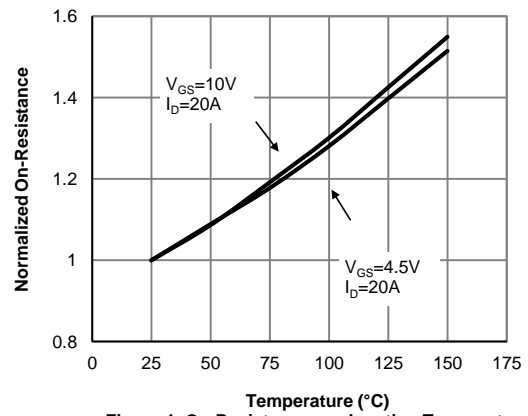


Figure 4: On-Resistance vs. Junction Temperature (Note E)

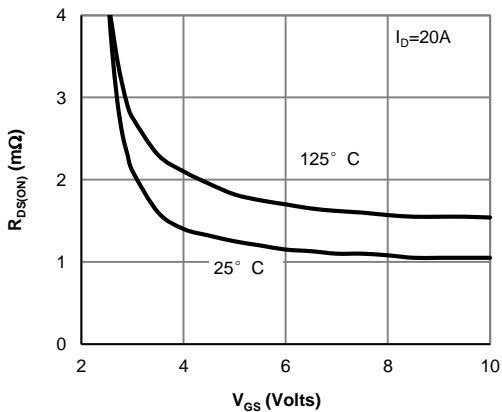


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

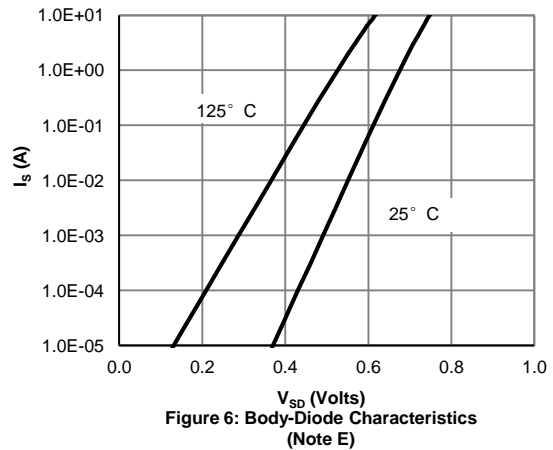


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

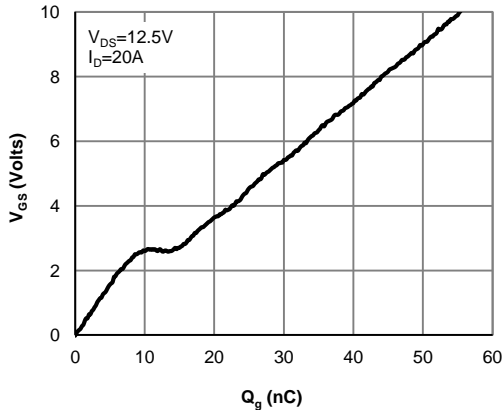


Figure 7: Gate-Charge Characteristics

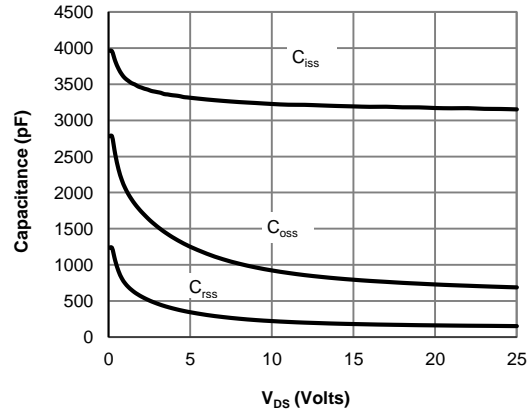


Figure 8: Capacitance Characteristics

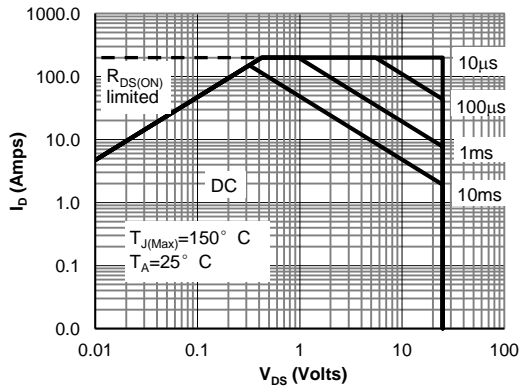


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

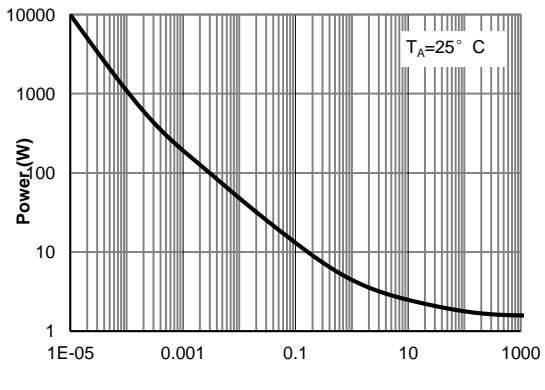


Figure 13: Single Pulse Power Rating Junction-to-Ambient (Note H)

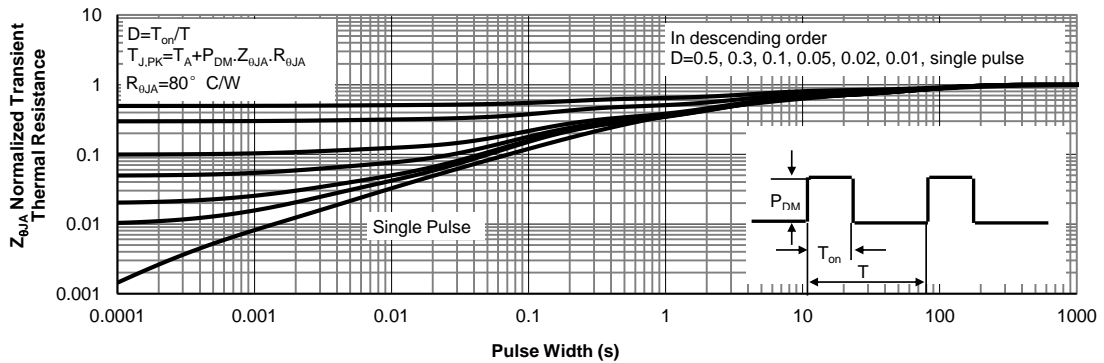


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

Figure A: Gate Charge Test Circuit & Waveforms

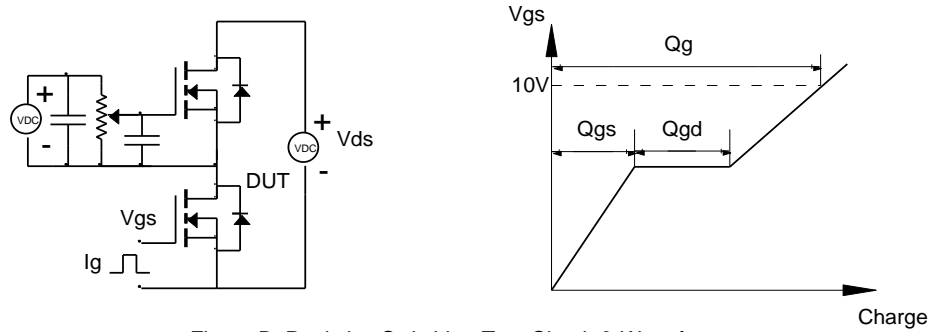


Figure B: Resistive Switching Test Circuit & Waveforms

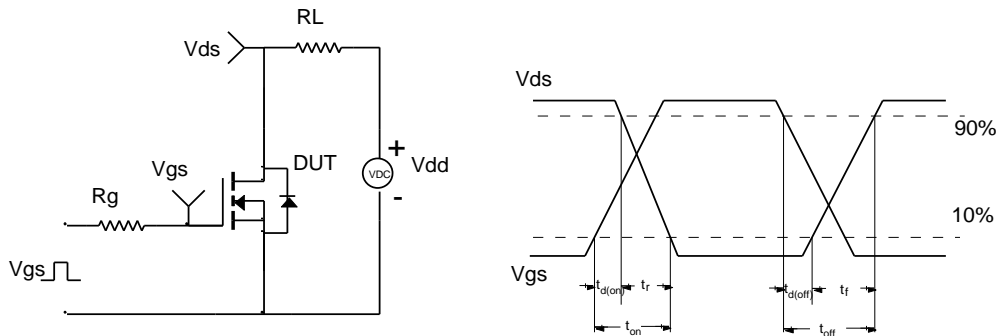


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

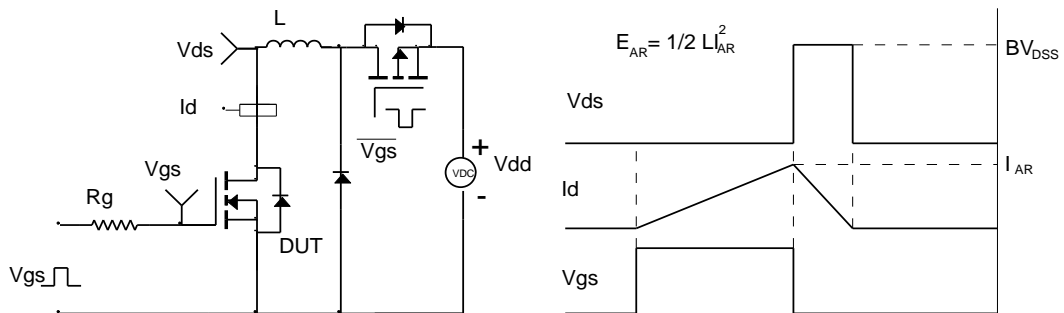


Figure D: Diode Recovery Test Circuit & Waveforms

